b.) Amendments to the Claims:

Please cancel Claim 2 without prejudice or disclaimer of the subject matter presented therein. Please amend Claim 6 and add new Claim 27, as follows. In accordance with the Revised Amendment Format, the status of all claims are presented below.

1. (Previously amended): A deposited-film formation method comprising the steps of:

providing a discharge electrode in a vacuum vessel equipped with exhaust means;

supplying a hydrogen gas and a raw material gas for forming a deposited film which contains at least an Si element;

generating plasma from the material gas by supplying high frequency electric power of 1 MHz to 200 MHz to the discharge electrode; and

forming a deposited film on a substrate in the vacuum vessel by plasma CVD,

wherein an auxiliary electrode is arranged in plasma in the vacuum vessel, and a periodically changing voltage having a voltage frequency of 1 MHz to 500 MHz and a maximum amplitude of 80V or less is applied to the auxiliary electrode to form a deposited film while controlling generation of hydrogen radicals.

2. (Cancelled).

3. (Original): The deposited-film formation method according to claim 2, wherein the maximum amplitude of the voltage is 20 V to 80 V.

4. (Original): The deposited-film formation method according to claim 2, wherein the maximum amplitude of the voltage is 20 V to 60 V.

5. (Original): The deposited-film formation method according to claim 1, wherein when the periodically changing voltage is applied to the auxiliary electrode, a voltage lower than the potential of plasma from the material gas is applied only in a certain period in at least one cycle of the periodically changing voltage.

6. (Currently amended): The deposited-film formation method according to claim 1, wherein a plurality of said auxiliary electrodes is arranged at least in a flow direction of the material gas.

7-8. (Cancelled).

9. (Original): The deposited-film formation method according to claim 1, wherein the auxiliary electrode is formed from an edgeless and small electrode having a small area facing a substrate in the vacuum vessel.

10. (Previously amended): The deposited-film formation method according to claim 1, wherein the auxiliary electrode is formed from a round bar which has a small diameter and which is made of a high strength material of a high melting point metal.

11. (Previously amended): A deposited-film formation method comprising the steps of:

providing a discharge electrode in a vacuum vessel equipped with exhaust means;

supplying a hydrogen gas and a raw material gas for forming a deposited film which contains at least an Si element;

generating plasma from the material gas by supplying high frequency electric power of 1 MHz to 200 MHz to the discharge electrode; and

forming a deposited film on a substrate in the vacuum vessel by plasma CVD,

wherein an auxiliary electrode is arranged in plasma in the vacuum vessel, a periodically changing voltage having a voltage frequency of 1 MHz to 500 MHz and a maximum amplitude of 80V or less is applied to the auxiliary electrode so that a voltage lower than the potential of plasma from the material gas is applied only in a certain period in at least one cycle of the periodically changing voltage, thereby forming a deposited film and controlling generation of hydrogen radicals.

12. (Previously amended): A deposited-film formation method comprising the steps of:

providing a discharge electrode in a vacuum vessel equipped with exhaust means;

supplying a hydrogen gas and a raw material gas for forming a deposited film which contains at least an Si element;

generating plasma from the material gas by supplying high frequency electric power to the discharge electrode; and

forming a deposited film on a substrate in the vacuum vessel by plasma CVD,

wherein an auxiliary electrode is arranged in plasma in the vacuum vessel, a high-frequency power of 1 MHz to 200 MHz is applied to the discharge electrode, and a high-frequency power of 1 MHz to 500 MHz and a maximum amplitude of 80V or less is applied to the auxiliary electrode, thereby forming a deposited film and controlling generation of hydrogen radicals.

13. (Previously amended): A deposited-film formation method comprising the steps of:

providing a discharge electrode in a vacuum vessel equipped with exhaust means;

supplying a hydrogen gas and a raw material gas for forming a deposited film which contains at least an Si element;

generating plasma from the material gas by supplying high frequency electric power of 1 MHz to 200 MHz to the discharge electrode; and

forming a deposited film on a substrate in the vacuum vessel by plasma CVD,

wherein an auxiliary electrode is arranged in plasma in the vacuum vessel, a periodic electric field having a voltage frequency of 1 MHz to 500 MHz and a maximum amplitude of 80V or less is applied to the auxiliary electrode, and only electrons are

energized without energizing ions to discompose a hydrogen gas and generate hydrogen radicals, thereby forming a deposited film and controlling the generation of the hydrogen radicals.

14 -26. (Withdrawn). cancelled

27. (New): The deposited-film formation method according to claim 1, wherein said auxiliary electrode is arranged in the plasma and between said discharge electrode and said substrate.